

BEST AVAILABLE COPY

Application Number: 10/604,573 Examiner: Shawn Riley Art Unit: 2838
(Currently amended) CLAIMS

January 10, 2005

What is claimed is:

1. (Currently amended) An integrated circuit package comprising:
a semiconductor die of plural separate power supply voltage domains; and
5 a switch mode DC-to-DC converter, including at least:
wherein said switch mode DC-to-DC converter comprises:
an inductor core and windings;
a power switching transistor; and
~~an a digital open-loop output voltage fixing circuit.~~

10

2. (Canceled)
3. (Canceled)

Office Action Reply Page 7 of 14

BEST AVAILABLE COPY

Application Number: 10/604,573 Examiner: Shawn Riley Art Unit: 2838 January 10, 2005

4. (Currently amended) An integrated circuit package comprising:a semiconductor die of plural separate power supply voltage domains; anda switch mode DC-to-DC converter,wherein said switch mode DC-to-DC converter comprises:an inductor core and windings;a power switching transistor; andan output voltage fixing circuit.

5

The integrated circuit of claim 1 wherein said semiconductor die comprises adecoder that compares an entry from a table corresponding to the present power state of10 said semiconductor die to a clock counter frequency divider output to determine dutycycle and/or switching frequency of said power switching transistor for said outputvoltage fixing circuit.15 5. (Currently amended) The integrated circuit of claim 4, wherein said table of
entries of clock counter values to determine duty cycle is encoded within logic within
said semiconductor die.20 6. (Currently amended) The integrated circuit of claim 4, wherein said table of
entries of clock counter values to determine duty cycle is contained within non-volatile
memory.

Application Number: 10/604,573 Examiner: Shawn Riley Art Unit: 2838 January 10, 2005

7. (Currently amended) The integrated circuit package of claim 14, wherein the power transistor gate-driving signal output from said semiconductor die is connected through a charge pump circuit to optimize efficiency of the power switching transistor of said DC-to-DC converter.

5

8. (Currently amended) The integrated circuit package of claim 14, also further comprising a substrate of fiberglass resin epoxy of type FR4 based laminate material for mounting said DC-to-DC converter components.

10 9. (Currently amended) The integrated circuit package of claim 8, wherein said semiconductor die contains further comprises a plurality of pads from which to accept a binary number offset for fine tuning the said duty cycle and/or switching frequency by modifying the value compared to the clock counter frequency divider in said output voltage fixing circuit of said DC-to-DC converter.

15

10. (Currently amended) The output voltage fixing circuit of claim 9, wherein said binary number offset is embodied within fusible leads on the said substrate that are electrically or mechanically trimmed or laser-trimmed at the factory.

20 11. (Currently amended) The output voltage fixing circuit of claim 9, wherein said binary number offset is embodied within a wire-bonding option during assembly of said semiconductor die pads to the lead frame of said integrated circuit package.

Office Action Reply Page 9 of 14

Application Number: 10/604,573 Examiner: Shawn Riley Art Unit: 2838 January 10, 2005

12. (Currently amended) The integrated circuit package of claim 8, wherein the power transistor gate driving signal output from said semiconductor die is connected through a trimmed delay circuit to fine tune the duty cycle of pulse width modulator or pulse frequency modulator of the output voltage fixing circuit of said DC-to-DC converter.

13. (Currently amended) The output voltage fixing circuit of claim 12, wherein said trimmed delay circuit further comprises a printed film resistor on the substrate that is laser-trimmed at the factory.

10

14. (Currently amended) An integrated circuit package comprising: a substrate of fiberglass resin epoxy of type FR4 based laminate material for mounting; a semiconductor die of plural separate power supply voltage domains; and a switch mode DC-to-DC converter including at least further comprising an inductor core and windings, a power switching transistor, and an a digital open-loop output voltage fixing circuit.

15. (Currently amended) The output voltage fixing circuit of claim 9, wherein said binary number offset is embodied within a wire-bonding option during assembly of said semiconductor die pads to ~~said substrate of claim 14~~ onto a substrate of fiberglass resin epoxy of type FR4 based laminate material.

Office Action Reply Page 10 of 10

BEST AVAILABLE COPY

Application Number: 10/604,573 Examiner: Shawn Riley Art Unit: 2838

January 10, 2005

16. (Currently amended) A method for design and fabrication of an integrated circuit package comprising a semiconductor die of plural separate power supply voltage domains with an integrated switch mode power supply, said method comprising steps of:

5 designing a semi-custom or standard cell library based digital core and obtaining from the design automation tools power consumption estimates in various power states given known clocking rates;

 determining switch mode power supply frequency, inductance, and duty cycles for various power states given the above said power consumption estimates and system

10 clocking;

 fabricating said semiconductor die for prototyping purposes, packaged without said integrated switch mode power supply;

 characterizing said prototype semiconductor die for power consumption over all operating power states and environmental conditions and process variations;

15 fabricating said switch mode power supply onto final production substrates;

 trimming the output voltage fixing circuit of said switch mode power supply after a probe test to determine the output voltages at given duty cycles versus output currents defined by the said semiconductor die known characterization data;

 bonding and molding or sealing with epoxy said semiconductor die and power

20 supply substrate into an integrated package.

BEST AVAILABLE COPY

Application Number: 10/604,573 Examiner: Shawn Riley Art Unit: 2838 January 10, 2005

17. (Currently amended) The method of claim 16, wherein said step of trimming the output voltage fixing circuit further comprises a ~~further~~ step of binning said final production power supply substrates into the appropriate wire-bonding assembly line to set the proper binary number offset of the output voltage fixing circuit.

5

18. (Currently amended) The method of claim 16, wherein said step of trimming the output voltage fixing circuit further comprises a ~~further~~ step of breaking fusible leads on said final production power supply substrate to set the binary number offset of the output voltage fixing circuit.

10

19. (Currently amended) The method of claim 16, wherein said step of trimming the output voltage fixing circuit further comprises a ~~further~~ step of laser trimming a printed film resistor forming a delay circuit of the output voltage fixing circuit on said final power supply substrate.

15

20. (Currently amended) The method of claim 16, wherein said step of trimming the output voltage fixing circuit further comprises a ~~further~~ step of programming a non-volatile memory with entries of clock counter values to determine duty cycle and/or switching frequency corresponding to each power state of the semiconductor die.

20

Office Action Reply Page 12 of 12 14

TEST AVAILABLE COPY

Application Number: 10/604,573 Examiner: Shawn Riley Art Unit: 2838 January 10, 2005

21. (Currently amended) A method for design and fabrication of an integrated circuit package comprising a semiconductor die of plural separate power supply voltage domains with an integrated switch mode power supply, said method comprising steps of:

designing a semi-custom or standard cell library based digital core and obtaining

5 from the design automation tools power consumption estimates in various power states given known clocking rates;

determining switch mode power supply frequency, inductance, and duty cycles for various power states given ~~above~~ said power consumption estimates and system clocking;

10 fabricating said semiconductor die for prototyping purposes, packaged without said integrated switch mode power supply;

characterizing said prototype semiconductor die for power consumption over all operating power states and environmental conditions and process variations;

15 fabricating said switch mode power supply onto final production substrates; bonding and molding or sealing with epoxy said semiconductor die and assembled final power supply substrate into an integrated package.

Office Action Reply Page 13 of 14